

ESH1PB, ESH1PC, ESH1PD

Vishay General Semiconductor

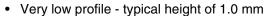
High Current Density Surface Mount Ultrafast Rectifiers



DO-220AA (SMP)

PRIMARY CHARACTERISTICS						
I _{F(AV)}	1.0 A					
V _{RRM}	100 V, 150 V, 200 V					
t _{rr}	25 ns					
V _F	0.90 V					
T _J max.	175 °C					

FEATURES





- · Ideal for automated placement
- · Glass passivated chip junction
- Ultrafast recovery times for high frequencyLow forward voltage drop, low power loss
 - RoHS

- Low thermal resistance
- Meets MSL level 1 per J-STD-020, LF maximum peak of 260 °C
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in secondary rectification and freewheeling for ultrafast switching speeds of ac-to-ac and dc-to-dc converters in high temperature conditions for both consumer and automotive applications.

MECHANICAL DATA

Case: DO-220AA (SMP)

Epoxy meets UL 94 V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: Color band denotes cathode end

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	ESH1PB	ESH1PC	ESH1PD	UNIT	
Device marking code		РВ	PC	PD		
Maximum repetitive peak reverse voltage	V _{RRM}	100	150	200	V	
Maximum average forward rectified current (Fig. 1)	I _{F(AV)}	1.0			Α	
Peak forward surge current 10 ms single half sine-wave superimposed on rated load	I _{FSM}	50			А	
Operating junction and storage temperature range	T _J , T _{STG}	- 55 to + 175			°C	

ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
Maximum instantaneous forward voltage (1)	I _F = 0.7 A I _F = 1 A	T _J = 25 °C	V _F	0.86 0.90	V	
Maximum reverse current at rated V _R voltage ⁽²⁾		T _J = 25 °C T _J = 125 °C	I _R	1.0 25	μΑ	
Maximum reverse current	V _R = 20 V	T _J = 150 °C	I _R	50	μΑ	

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
Maximum reverse recovery time	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$	t _{rr}	25	ns			
Typical reverse recovery time	$I_F = 1.0 \text{ A}, V_R = 30 \text{ V},$ $dI/dt = 50 \text{ A/µs}, I_{rr} = 10 \% I_{RM}$	T _J = 25 °C T _J = 100 °C	t _{rr}	25 35	ns		
Typical stored charge	$I_F = 1.0 \text{ A}, V_R = 30 \text{ V},$ $dI/dt = 50 \text{ A/µs}, I_{rr} = 10 \% I_{RM}$	T _J = 25 °C T _J = 100 °C	Q _{rr}	10 15	nC		
Typical junction capacitance	4.0 V, 1 MHz		CJ	25	pF		

Notes:

(1) Pulse test: 300 μ s pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	ESH1PB	ESH1PC	ESH1PD	UNIT
Typical thermal resistance ⁽¹⁾	$egin{aligned} R_{ hetaJA} \ R_{ hetaJL} \ R_{ hetaJC} \end{aligned}$		105 15 20		°C/W

Note:

(1) Thermal resistance from junction to ambient and junction to lead mounted on P.C.B. with 5.0 x 5.0 mm copper pad areas. $R_{\theta JL}$ is measured at the terminal of cathode band. $R_{\theta JC}$ is measured at the top center of the body

ORDERING INFORMATION (Example)						
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
ESH1PB-E3/84A	0.024	84A	3000	7" diameter plastic tape and reel		
ESH1PB-E3/85A	0.024	85A	10 000	13" diameter plastic tape and reel		
ESH1PBHE3/84A (1)	0.024	84A	3000	7" diameter plastic tape and reel		
ESH1PBHE3/85A (1)	0.024	85A	10 000	13" diameter plastic tape and reel		

Note:

(1) Automotive grade AEC Q101 qualified

RATINGS AND CHARACTERISTICS CURVES

 $(T_A = 25 \, ^{\circ}C \text{ unless otherwise noted})$

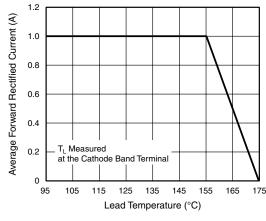


Figure 1. Forward Current Derating Curve

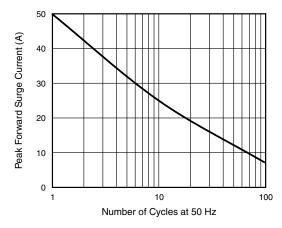


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current





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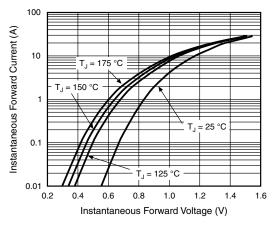


Figure 3. Typical Instantaneous Forward Characteristics

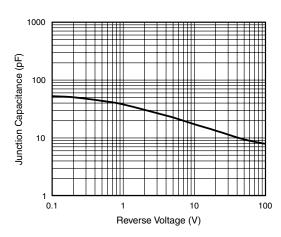


Figure 5. Typical Junction Capacitance

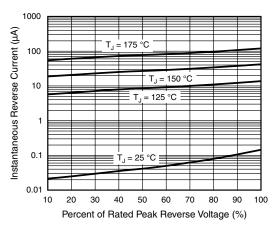


Figure 4. Typical Reverse Leakage Characteristics

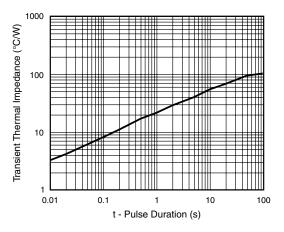
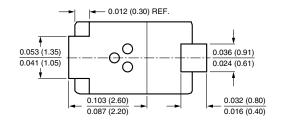
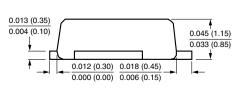


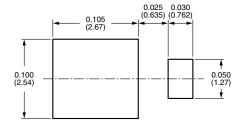
Figure 6. Typical Transient Thermal impedance

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

0.086 (2.18) 0.074 (1.88) 0.142 (3.61) 0.126 (3.19) 0.158 (4.00) 0.146 (3.70)







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